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# Development of TaichuPix prototypes for the CEPC vertex detector

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On behalf of the CEPC MOST2 Vertex detector design team

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# Outline

- **Project motivation and TaichuPix chip overview**
- **Small scale prototypes design and test results**
- **Full size chip design**
- **Summary**

# MOST2 project requirements on pixel chip

## Silicon Vertex Detector **Prototype** – MOST (2018–2023)

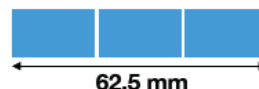
### Sensor technology CMOS TowerJazz

- Design sensor with large area and high resolution
- Integration of front-end electronic on sensor chip



Double sided ladder

Layer 1 (11 mm x 62.5 mm)  
Chip size: 11 mm X 20.8 mm

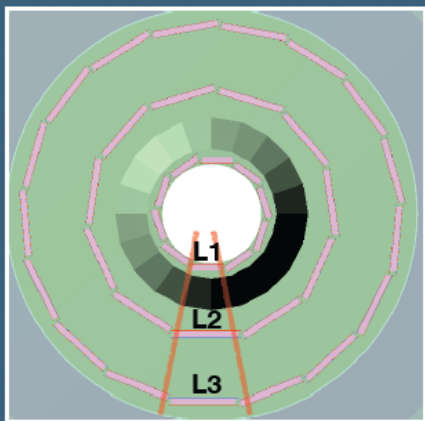


3 X 2 layer = 6 chips

Benefit from MOST 1 research program

Ref: Introduction to the Pixel MOST2 Project, Joao Costa, 2018.6

### 3-layer sector



Baseline MOST2 goal:  
3-layer prototype

Default layout requires different size ladders

Keep it simple for baseline design

L1

L2

L3

3-layers  
same size  
same chip

### Goals:

1 MRad TID

3-5 $\mu$ m SP resolution

Integrate electronics  
readout

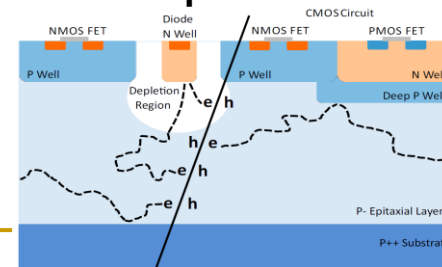
Design and produce  
light and rigid  
support structures

8

## Motivation for **TaichuPix** chip design

- Large-scale & full functionality pixel chip
- Fit to be assembled on ladders with backend Elec. & DAQ

### CMOS pixel sensor



# Main specs of the full size chip for high rate vertex detector

## ■ Bunch spacing

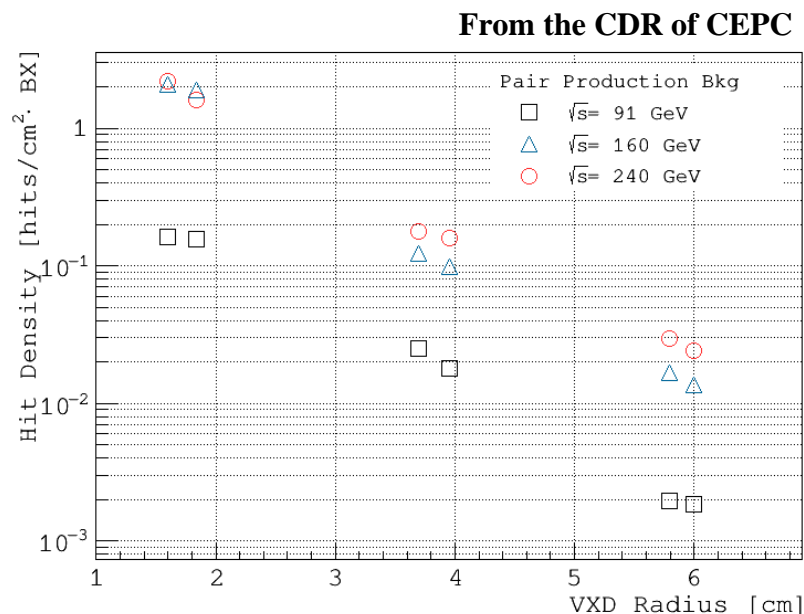
- Higgs: 680 ns; W: 210 ns; Z: **25 ns**
- Meaning 40M/s bunches (same as the ATLAS Vertex)

## ■ Hit density

- 2.5 hits/bunch/cm<sup>2</sup> for Higgs/W; 0.2 hits/bunch/cm<sup>2</sup> for Z

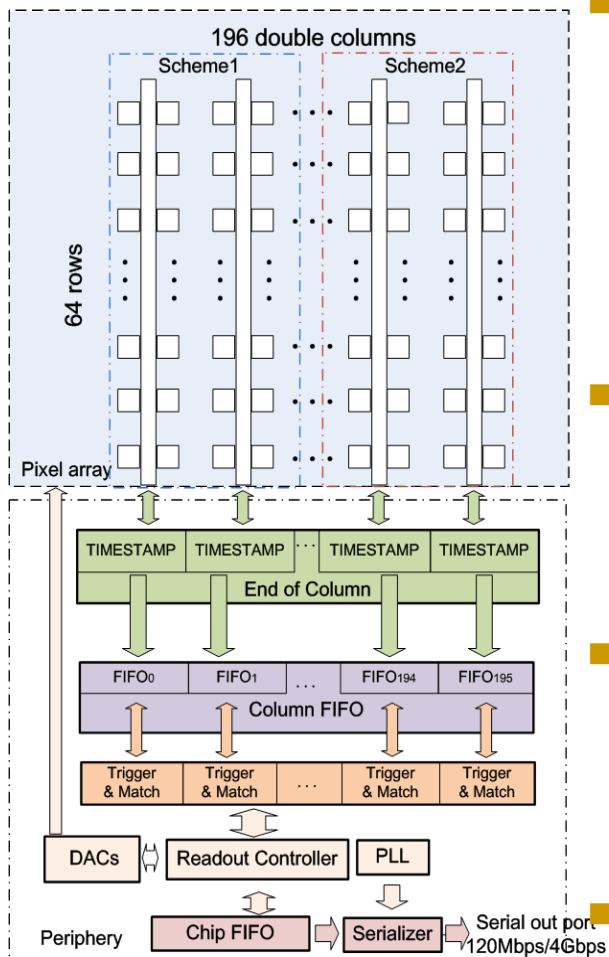
## ■ Cluster size: 3pixels/hit

- Epi-layer thickness: ~18 μm
- Pixel size: 25 μm × 25 μm



For Vertex	Specs	For High rate Vertex	Specs	For Ladder Prototype	Specs
Pixel pitch	<b>&lt;= 25 μm</b>	Hit rate	<b>120 MHz/chip</b>	Pixel array	512 row × 1024 col
TID	<b>&gt;1 Mrad</b>	Date rate	<b>3.84 Gbps</b> --triggerless <b>~110 Mbps</b> --trigger	Power Density	<b>&lt; 200 mW/cm<sup>2</sup></b> (air cooling)
		Dead time	<b>&lt; 500 ns</b> --for 98% efficiency	Chip size	<b>~1.4 cm×2.56 cm</b>

# TaichuPix architecture



- **Similar to the ATLAS ITK readout architecture: “column-drain” readout**

- Priority based data driven readout, zero-suppression intrinsically
- Modification: **time stamp is added at EOC** whenever a new fast-or busy signal is received
- **Dead time:** 2 clk for each pixel (50 ns @40MHz clk)

- **Two parallel pixel digital schemes**

- ALPIDE-like: Readout speed was enhanced for 40MHz BX
- FE-I3-like: Fully customized layout of digital cells and address decoder for smaller area

- **2-level FIFO architecture**

- L1 FIFO: In column level, to de-randomize the injecting charge
- L2 FIFO: Chip level, to match the in/out data rate between the core and interface

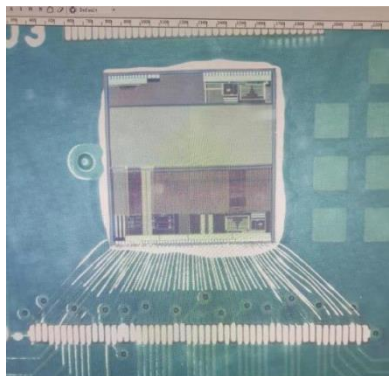
- **Trigger readout**

- Make the data rate in a reasonable range
- Data coincidence by time stamp, only matched event will be readout

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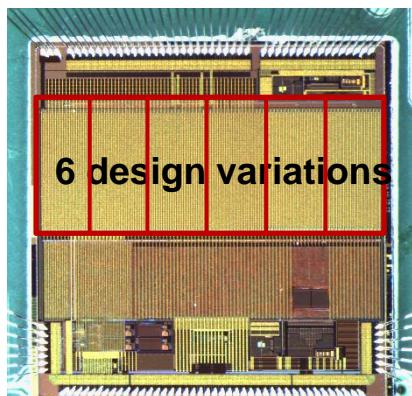
# TaichuPix small prototypes overview



**TaichuPix-1**

**Chip size: 5 mm × 5 mm**

**Pixel size: 25 μm × 25 μm**



**TaichuPix-2**

**Chip size: 5 mm × 5 mm**

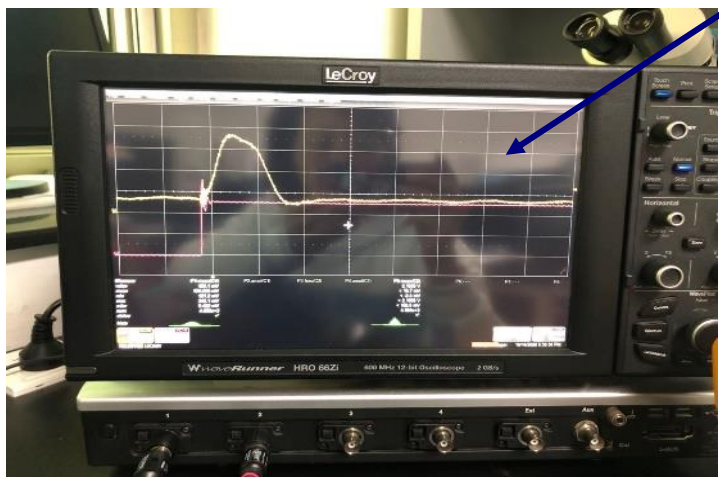
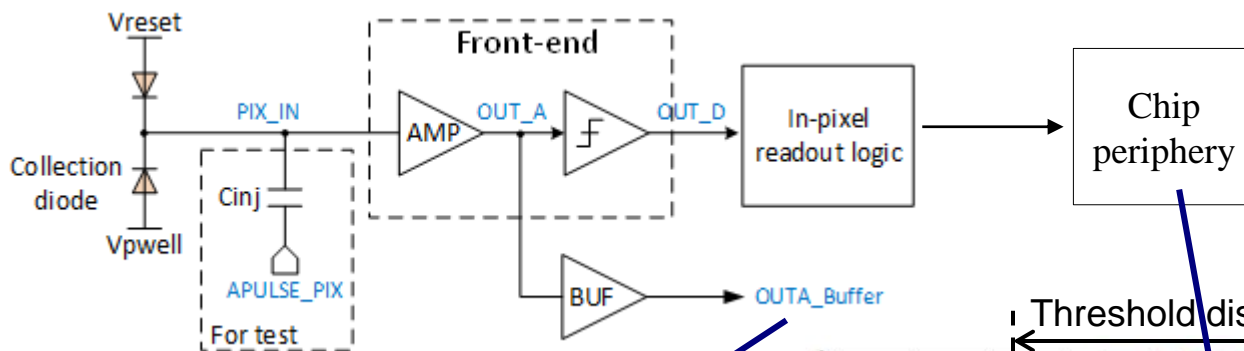
**Pixel size: 25 μm × 25 μm**

- **Two MPW chips were fabricated and verified**
  - TaichuPix-1: 2019.06~2019.11
  - TaichuPix-2: 2020.02~2020.06
- **Chip size 5 mm×5 mm with standalone features**
  - In-pixel circuitry:
    - Continuously active front-end
    - Two digital schemes, with masking & testing config. logics
  - A full functional pixel array (64×192 pixels)
  - Periphery logics
    - Fully integrated logics for the **data-driven readout**
    - Fully digital control of the chip configuration
  - Auxiliary blocks for standalone operation
    - **High speed data interface** up to 4 Gbps
    - On-chip bias generation
    - Power management with LDOs
    - IO placement in the final ladder manner
      - Multiple chip interconnection features included

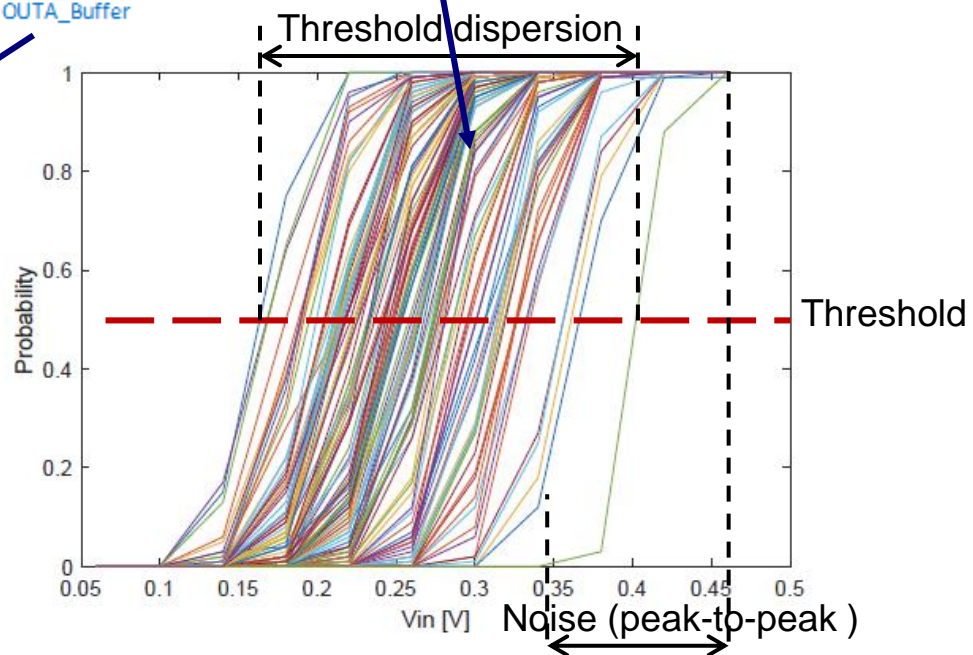


# Electrical test

- Electrical performance verified by injecting external voltage pulses into pixel front-end



Analog output of a pixel @  $V_{in} = 0.9 \text{ V}$



Measured "S-curve" for 128 pixels

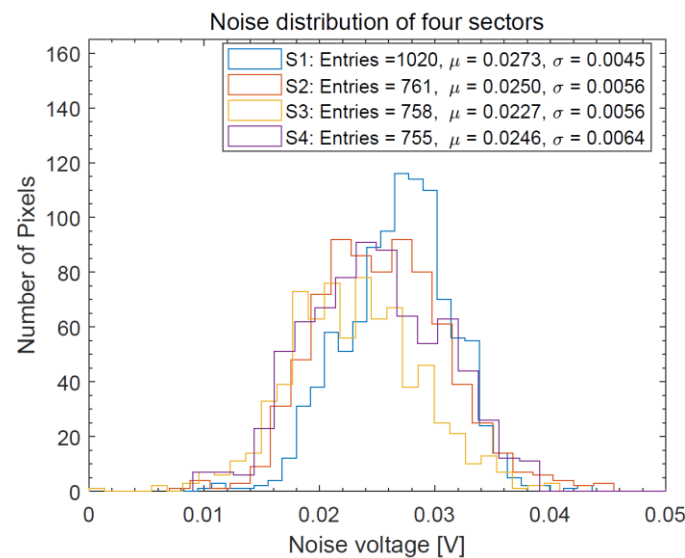
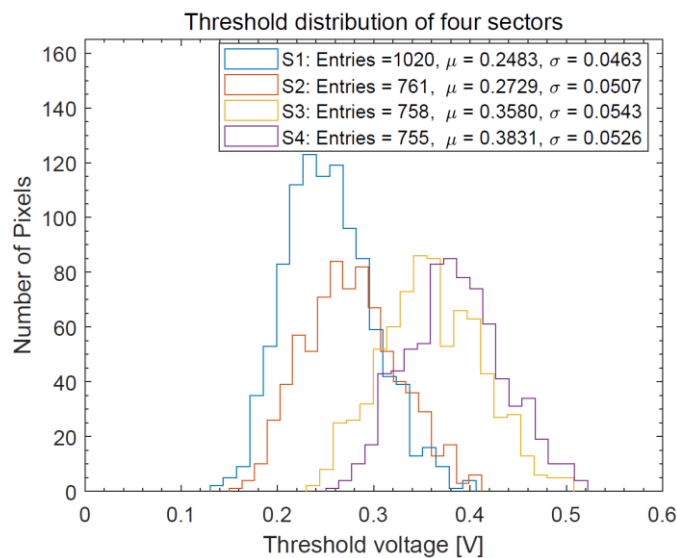


# Performance of threshold and noise of TaichuPix2

## ■ Bias setting: ITHR = 6.2 nA, VSUB = 0 V

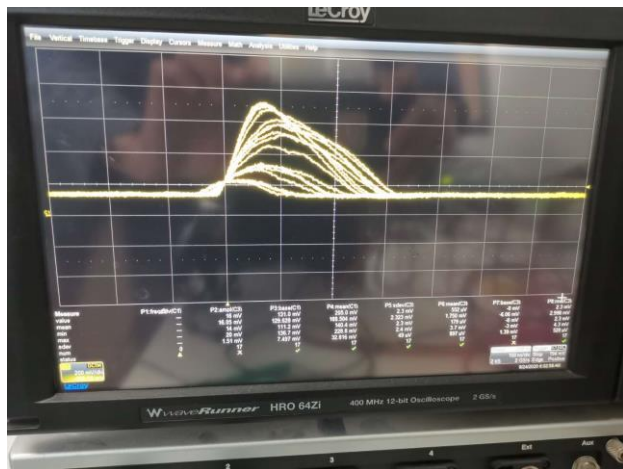
- Threshold can be tuned by changing ITHR (a global current bias)

Chip4	Threshold Mean (e-)	Threshold rms (e-)	Temporal noise (e-)	Total equivalent noise (e-)
S1	272.9	50.9	30.0	59.1
S2	299.9	55.7	27.5	62.1
S3	393.4	59.7	24.9	64.7
S4	421.0	57.8	27.0	63.8

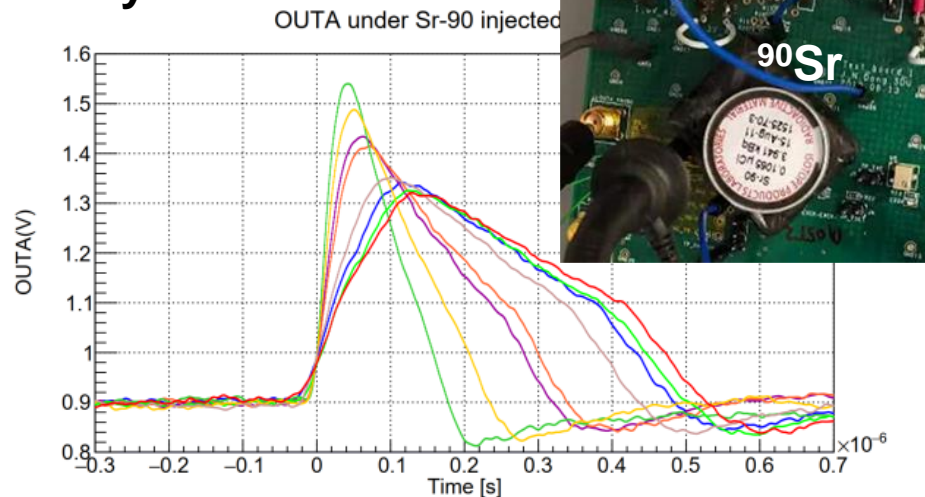


# TaichuPix response to radioactive

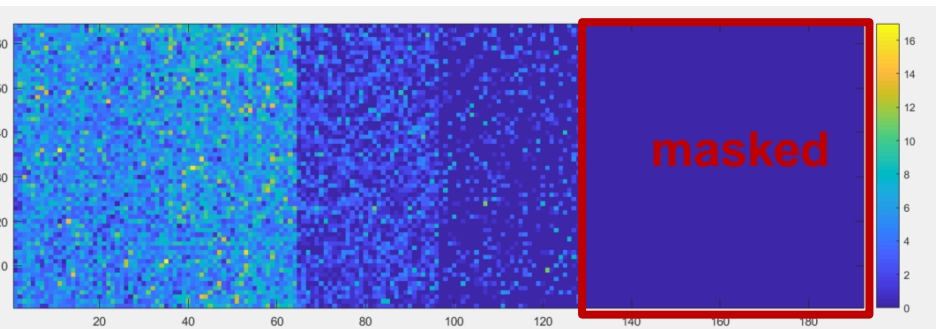
- Functionality of TaichuPix1&2 proved by various tests



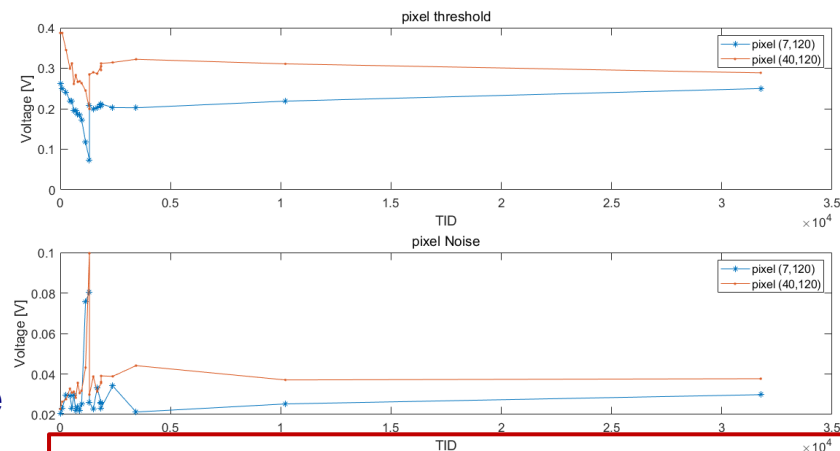
Analog output of a pixel response to **X-ray** tube



Analog output with **<sup>90</sup>Sr** exposure



**X-ray** imaging with 5 min exposure @ 8 kV X-ray tube



Good chip functionality and noise performance proved up to **30 Mrad TID**

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# Overview of the full size engineering run

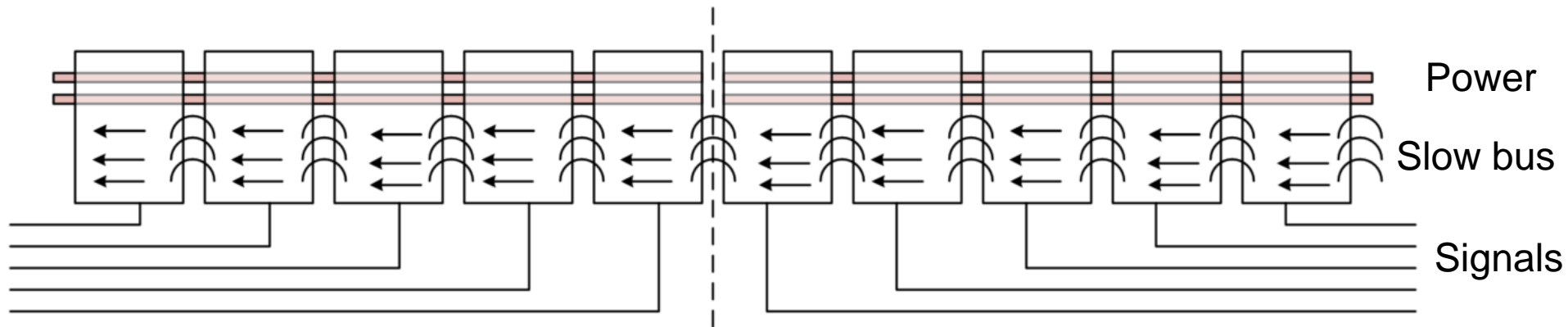
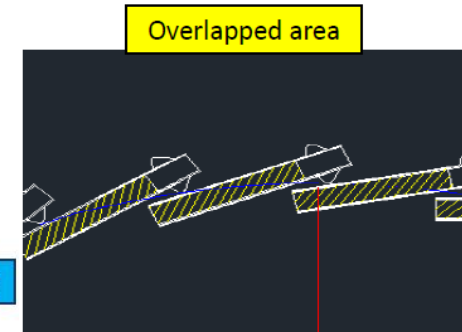
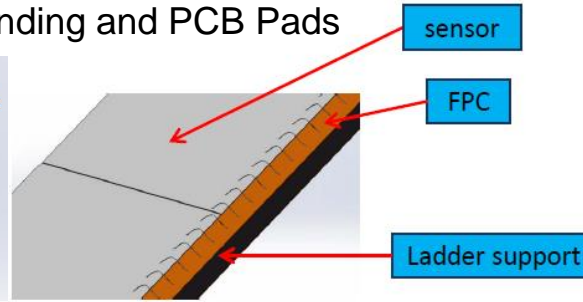
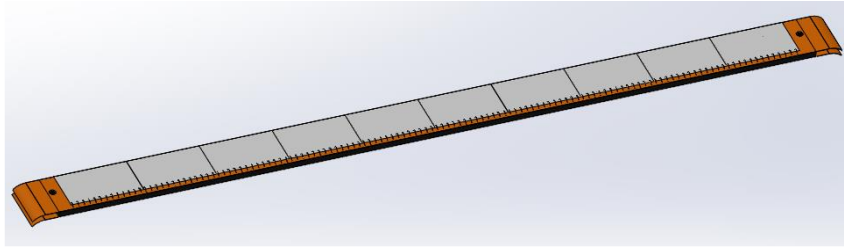


1. Pixel array  
1024\*512
2. Periphery
3. DAC & Bias generation
4. Data interface
5. LDO (test blocks)
6. Chip inter-connection features
7. Scribe-able top power connection features

- Process: 180 nm CMOS Imaging Sensor process (7 metal layers)
- Pixel cell copied exactly from MPW + scaled logic with new layout  
Periphery + debugged/improved blocks + enhanced power network

# Flex cable design consideration

2mm margin for wire bonding and PCB Pads

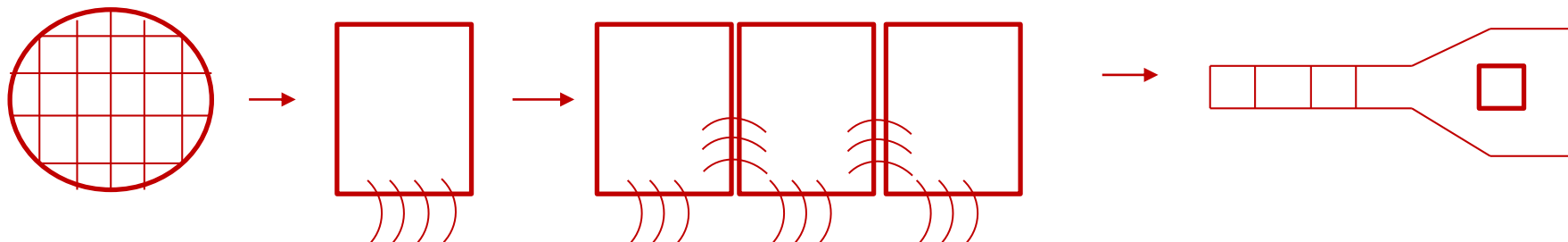


## ■ Design goals & considerations for the Flex PCB

- Minimum material budget
  - Minimum dead zone extension, limited height of PCB
    - ❑ Minimum set of signals on Flex
    - ❑ Slow buses to go on chip area by chip interconnection buses
  - Robust power supply
- Manufacturability

# Testability design & test plan consideration

- All test features reserved, while the connected IOs will decrease at diff stages depending on chip test & study results
  - Analog probe signals at the top part, accessible from the top pads
  - When mounted on ladder, only minimum self test possibilities can be reserved
- 1. **Probe Card design for the wafer test**
  - For all the pads at both sides
- 2. **Single chip test board design**
  - Designed with all the test features for the chip functional study
- 3. **Multiple chip test board for the ladder debugging**
  - Designed following the same manner as the ladder but on PCB
  - Signals and power supplies will be limited just with the ladder's dimension
  - Extra test signals can be connected to the extended area, to help debugging
- 4. **The real flex cable design for the ladder**
  - Core design and lessons will be exported from 3



# Summary

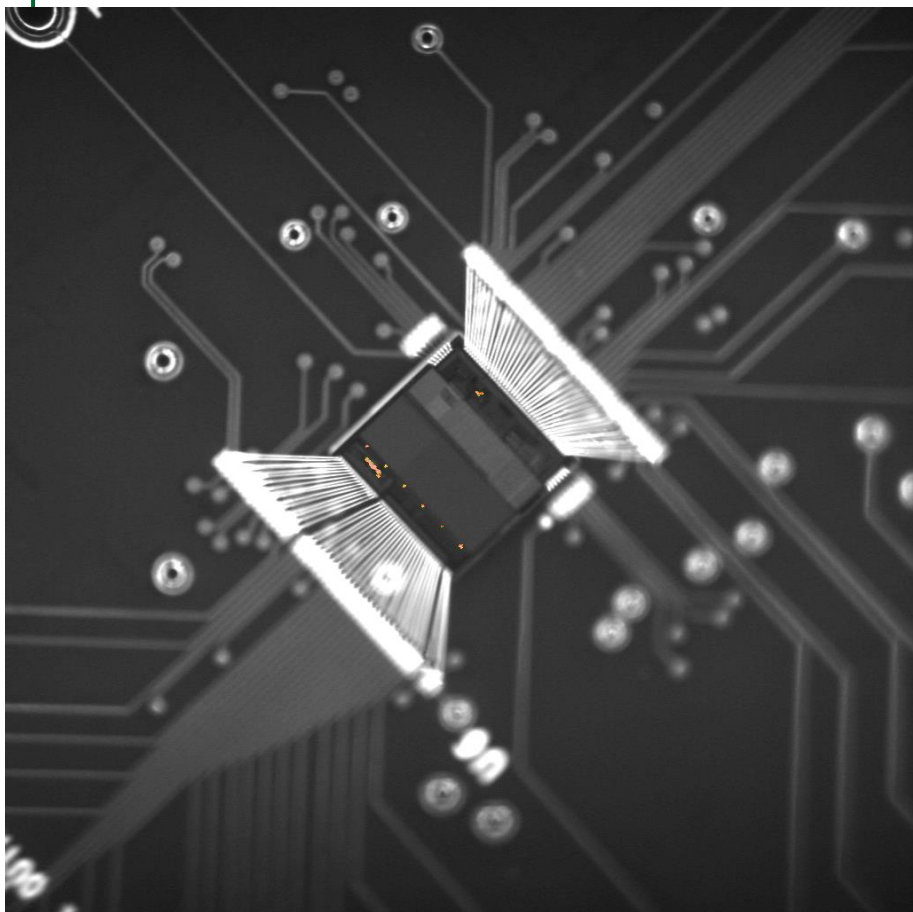
- **TaichuPix small prototypes were fully verified and preparing to submit the full size tape-out**
  - Full signal chain & functionality verified with both electrical & radioactive test
  - TID performance satisfied with CEPC's requirement with a large headroom
  - Full size chip design finished
  
- **Recent plan**
  - Design will be submitted for the engineering run
  - Preparation for the chip test (probe card, test PCB, flex cable ...)

**Thank you for your attention!**



# Backup

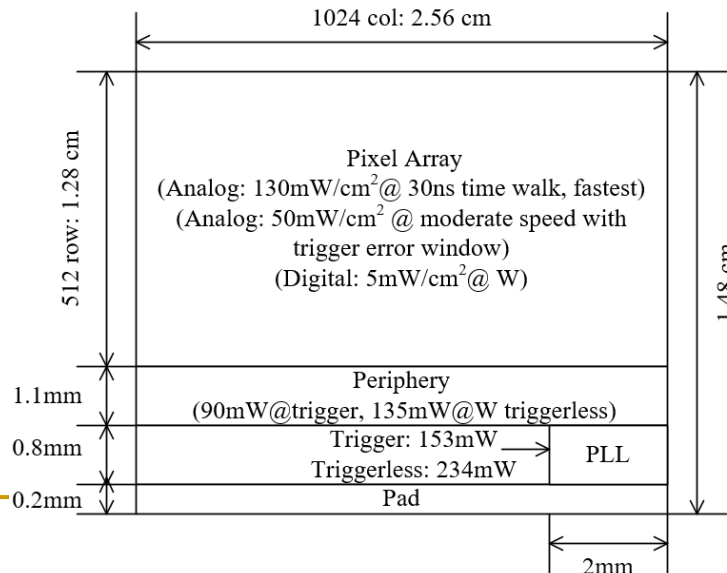
# Chip Power consuming test



- Tcpx2 chip current consuming tested of 210mA (380mW@1.8V)
- Almost agreed with simulation
  - PLL@trigger speed: 306mW
    - Read by triggerless but at 160Mbps
    - Two PLLs in Tcpx2
  - Analog biased at fastest: 15mW (192\*64 pixel array)
    - With 16 probe buffers
  - Periphery@trigger speed: 90mW
    - Read by triggerless but at 160Mbps

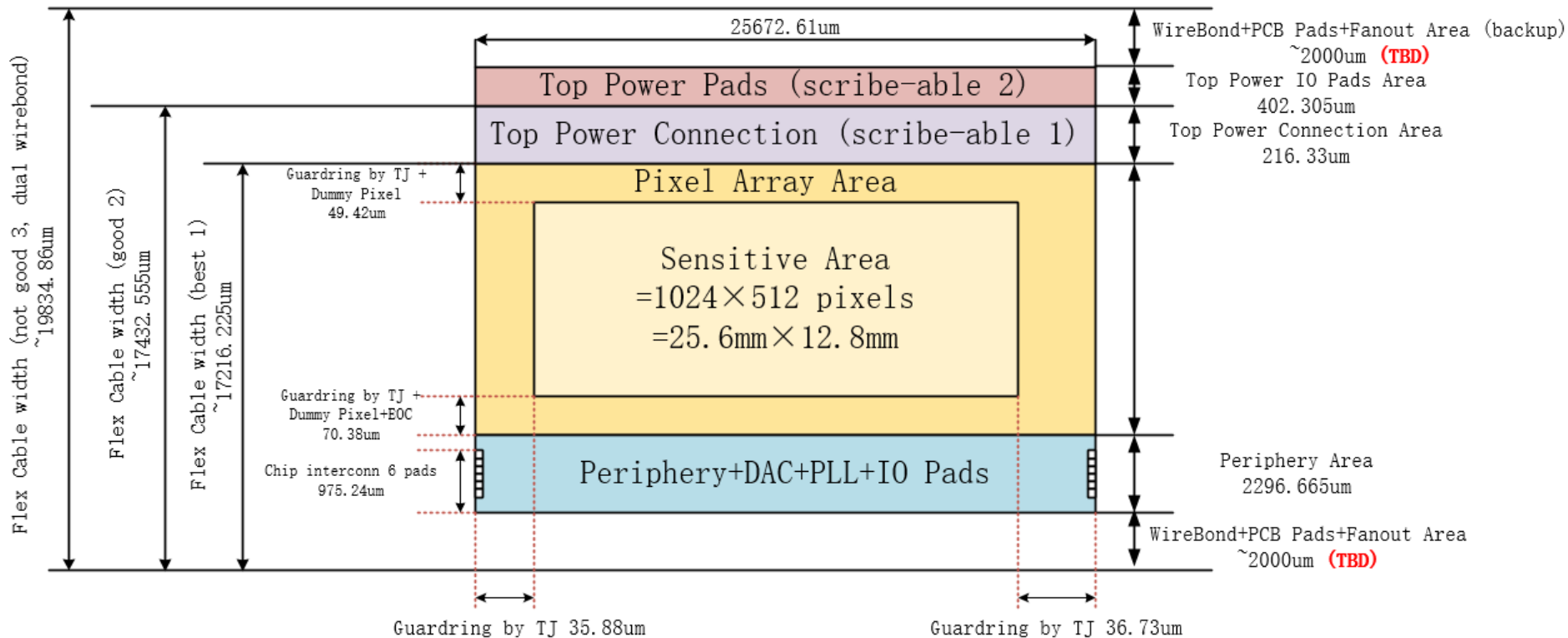
- The EMMI (Emission Microscope) test showed the hot points were exactly as expected

- quiet pixel array & periphery = no leakage point

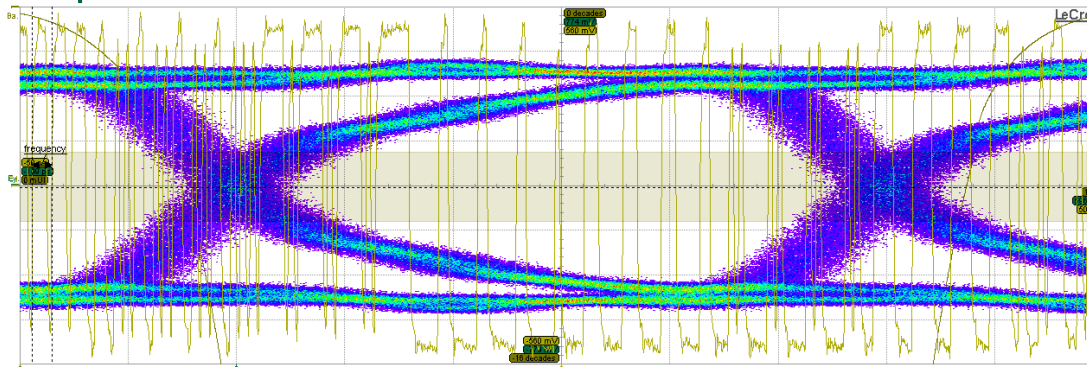


# Full size chip dimension

All the four edges need at least  
~50um for chip dicing remains



# Test of the data interface



**@2.24Gbps**

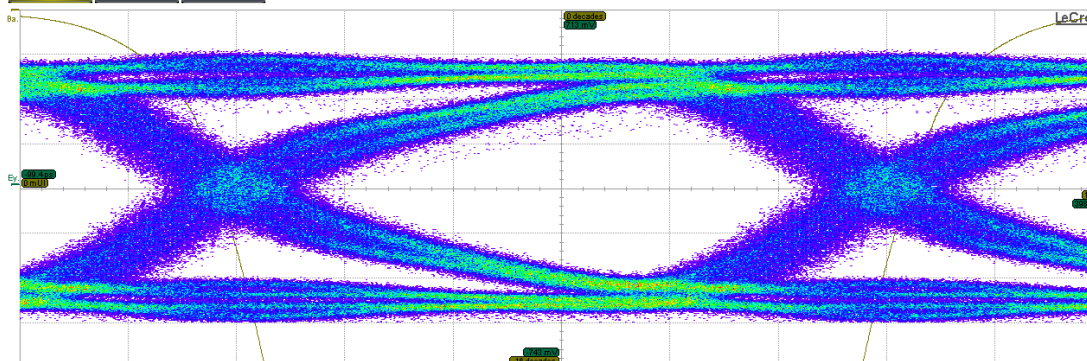
Measure	P1:freq(C1)	P2:ampl(C1)	P3:base(C1)	P4:top(C1)	P5:erms(Eye)	P6:epj(Eye)	P7:Q(Eye)	P8:pdcd(Eye)	P9:...	P10:...	P11:...	P12:...
value	1.12160 GHz	989.6 mV	-500.4 mV	489.2 mV	15.7 ps	106.3 ps	8.5436	39e-3				
mean	697.1421 MHz	> 968.105 mV	< -486.665 mV	> 481.440 mV	15.679 ps	106.297 ps	8.543596	39.08e-3				
min	1.7092 MHz	> 926.4 mV	< -502.7 mV	> 463.4 mV	15.7 ps	106.3 ps	8.5436	39e-3				
max	1.15117 GHz	> 995.3 mV	< -459.0 mV	> 493.3 mV	15.7 ps	106.3 ps	8.5436	39e-3				
sdev	288.6860 MHz	> 18.188 mV	< 12.536 mV	> 8.534 mV	---	---	---	---				
num	8.676e+3	155	155	155	1	1	---	---				
status												

SDA Jitter	Tj(e-12)	Rj(sp)	Dj(sp)	BitRate	Pj	ISI	DCD	DDj
value	141.63 ps	5.39 ps	64.77 ps	2.2400 Obit/sec	15.80 ps	45 ps	3 ps	48 ps
status								

SDA Eye	EyeHeight	EyeOne	EyeZero	EyeAmpl	EyeWidth	EyeCross	EyeAvgPwr	MaskHits	EyeBER
value	583.5 mV	441.8 mV	-457.5 mV	899.3 mV	352.2 ps	2.2 mV	---	1.363091e+6	6.59283502e-10
status									



**@3.36Gbps**

Measure	P1:freq(C1)	P2:ampl(C1)	P3:base(C1)	P4:top(C1)	P5:erms(Eye)	P6:epj(Eye)	P7:Q(Eye)	P8:pdcd(Eye)	P9:epj(Eye)	P10:...	P11:...	P12:...
value	1.1076 GHz	> 889.8 mV	< -460.9 mV	428.9 mV	16.2 ps	115.0 ps	7.0496	18e-3				
mean	1.036750 GHz	> 903.732 mV	< -466.151 mV	> 437.581 mV	16.2 ps	115.034 ps	7.049625	18.14e-3				
min	255.2 MHz	> 850.4 mV	< -541.6 mV	> 349.9 mV	16.2 ps	115.0 ps	7.0496	18e-3				
max	1.8142 GHz	> 979.1 mV	< -421.1 mV	> 483.3 mV	16.2 ps	115.0 ps	7.0496	18e-3				
sdev	447.550 MHz	> 26.016 mV	< 20.392 mV	> 14.592 mV	---	---	---	---				
num	14.389e+3	173	173	173	1	1	---	---				
status												

SDA Jitter	Tj(e-12)	Rj(sp)	Dj(sp)	BitRate	Pj	ISI	DCD	DDj
value	123.27 ps	4.84 ps	54.26 ps	3.3600 Obit/sec	7.15 ps	51 ps	1 ps	51 ps
status								

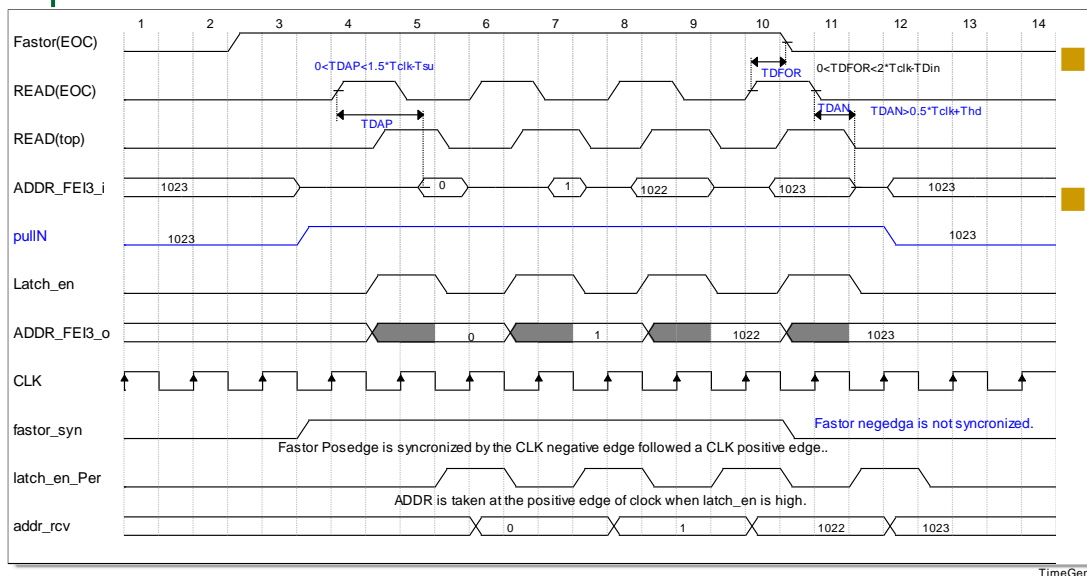
  

SDA Eye	EyeHeight	EyeOne	EyeZero	EyeAmpl	EyeWidth	EyeCross	EyeAvgPwr	MaskHits	EyeBER
value	479.8 mV	404.1 mV	-431.1 mV	835.2 mV	200.3 ps	50.01 %	-11.4 mV	1.524591e+6	914.388622e-15
status									

Bit rate	2.24Gbps	3.36Gbps	4.48Gbps
Clk freq	1.12GHz	1.68GHz	2.24GHz
BER	6.59e-18	9.14e-13	3.23e-5
Tj@e-12	141.63ps	123.27ps	147.14ps
Rj	5.39ps	4.84ps	5.35ps
Dj	64.77ps	54.26ps	70.90ps

- Data readout in DDR mode
- Data interface was tested by the on chip PRBS source, a high speed oscilloscope (@16Gbps), and code stream verified in FPGA
- **BER qualified till 3.36 Gbps, failed at 4.48 Gbps**
- Concerning the highest data rate for triggerless at 4Gbps, at least 2 SER interface ports needed
- Thus bit rate @2.24Gbps is safe and power optimized

# Readout & Periphery



Time stamp recorded when Fastor is valid

Each pixel readout by 2 clocks (50ns)

Worst delay ~ 25ns

➤ Sim by 512 rows (full size)

➤ TDA: read sent –addr come

Address latch @ 37.5ns

➤ @ 1.5 clock

➤ Enough headroom for all corners

## Designed for low power

- Only the hit (fastor) info & address are fannout from the pixel array
- Only the read (acquisition) signal is fanned in to the pixel array
  - Clock & time stamp are localized only in the EOC, different from FE-I3

## Optimized @ CEPC hit rate

- Common time stamp recorded for a full double column
  - For low power
  - Column is hit every 8.3us / pixel is readout in 2 clocks (50ns) / cluster size 3 pixels
  - Dead time 500ns – 98% trigger efficiency

